AP60G02NF

20V N+P-Channel Enhancement Mode MOSFET

Description

The AP60G02NF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

V_{DS} = 20V I_D =65A

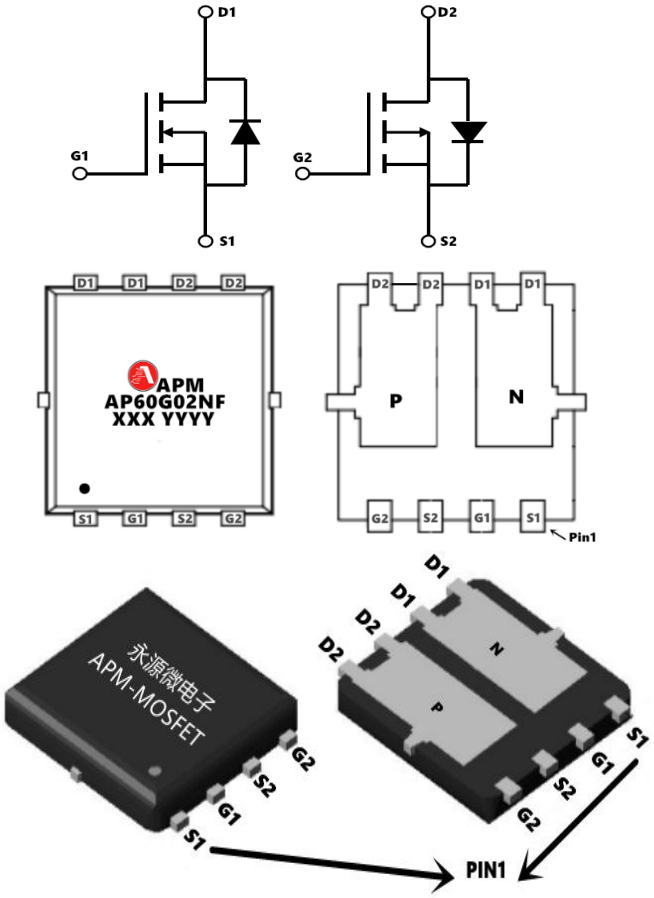
$R_{DS(ON)}$ < 6.5mΩ @ V_{GS}=4.5V（**Type：4.8mΩ**）

V_{DS} = -20V I_D =-62A

$R_{DS(ON)}$ < 8.5mΩ @ V_{GS}=-4.5V（**Type：6.8mΩ**）

Application

BLDC



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
AP60G02NF	PDFN5*6-8L	AP60G02NF XXX YYYY	5000

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Symbol	Parameter	N-Ch	P-Ch	Unit
VDS	Drain-Source Voltage	20	-20	V
VGS	Gate-Source Voltage	±12	±12	V
I_D@T_C=25℃	Continuous Drain Current, V_{GS} @ 10V[1]	65	-62	A
I_D@T_C=100℃	Continuous Drain Current, V_{GS} @ 10V[1]	42.5	-37.5	A
IDM	Pulsed Drain Current[2]	243	-210	A
EAS	Single Pulse Avalanche Energy[3]	389	478	mJ
IAS	Avalanche Current	30	25	A
P_D@T_C=25℃	Total Power Dissipation[4]	46		W
TSTG	Storage Temperature Range	-55 to 150		℃
T_J	Operating Junction Temperature Range	-55 to 150		℃
R_{θ}JA	Thermal Resistance Junction-Ambient [1]	25		℃/W
R_{θ}JC	Thermal Resistance Junction-Case[1]	1.3		℃/W

N-Electrical Characteristics (T_C=25℃unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
V(BR)DSS	Drain-Source Breakdown Voltage	VGS=0V, ID=250μA	20	24	-	V
IDSS	Zero Gate Voltage Drain Current	VDS=20V, VGS=0V,	-	-	1.0	μA
IGSS	Gate to Body Leakage Current	VDS=0V, VGS=±12V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID=250μA	0.5	0.7	1.2	V
RDS(on)	Static Drain-Source on-Resistance note3	VGS=4.5V, ID=20A	-	4.8	6.5	mΩ
		VGS=2.5V, ID=15A	-	5.8	8.0	
Ciss	Input Capacitance	VDS=10V, VGS=0V, f = 1.0MHz	-	2500	-	pF
Coss	Output Capacitance		-	407	-	pF
Crss	Reverse Transfer Capacitance		-	386	-	pF
Qg	Total Gate Charge	VDS=10V, ID=30A, VGS=4.5V	-	32	-	nC
Qgs	Gate-Source Charge		-	3	-	nC
Qgd	Gate-Drain(“Miller”) Charge		-	11	-	nC
td(on)	Turn-on Delay Time	VDS=10V, ID=30A, RGEN=3Ω, VGS =4.5V	-	17	-	ns
tr	Turn-on Rise Time		-	49	-	ns
td(off)	Turn-off Delay Time		-	74	-	ns
tf	Turn-off Fall Time		-	26	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	75	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	300	A
VSD	Drain to Source Diode Forward Voltage	VGS = 0V, IS=30A	-	-	1.2	V

Note :

1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3、The power dissipation is limited by 150℃ junction temperature
4、EAS condition: TJ=25℃, VDD =16V,V GS =4.5V ,L=0.1mH，RG=25Ω，ID=30A
5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

P-Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
V(BR)DSS	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D= -250μA	-20	-	-	V
IDSS	Zero Gate Voltage Drain Current	V_{DS} = -20V, V_{GS} = 0V,	-	-	-1	μA
IGSS	Gate to Body Leakage Current	V_{DS} =0V, V_{GS} = ±12V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	V_{DS}= V_{GS}, I_D= -250μA	-0.35	-0.65	-1.0	V
RDS(on)	Static Drain-Source on-Resistance note3	V_{GS} =-4.5V, I_D =-15A	-	6.8	8.5	mΩ
		V_{GS} =-2.5V, I_D =-12A	-	8.9	10	
C_{iss}	Input Capacitance	V_{DS} =-10V, V_{GS} =0V, f = 1.0MHz	-	4590	-	pF
Coss	Output Capacitance		-	505	-	pF
Crss	Reverse Transfer Capacitance		-	440	-	pF
Q_g	Total Gate Charge	V_{DS} =-10V, I_D =-15A, V_{GS} =-4.5V	-	46	-	nC
Q_{gs}	Gate-Source Charge		-	7.3	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	10	-	nC
td(on)	Turn-on Delay Time	V_{DD} =-10V, I_D =-14A, R_{GEN}=2.7Ω, V_{GS} =-10V	-	8	-	ns
t_r	Turn-on Rise Time		-	59	-	ns
td(off)	Turn-off Delay Time		-	111	-	ns
t_f	Turn-off Fall Time		-	43	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	-60	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-240	A
VSD	Drain to Source Diode Forward Voltage	V_{GS} = 0V, I_S =-20A	-	-	-1.2	V
trr	Reverse Recovery Time	T_J=25℃,I_{SD}=-15A, V_{GS}=0V di/dt=-100A/μs	-	18	-	ns
Qrr	Reverse Recovery Charge		-	7.7	-	nC

Note :

1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.

2、The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%

3、The power dissipation is limited by 150℃ junction temperature

4、EAS condition: TJ=25℃, VDD =-16V,V GS =-4.5V ,L=0.1mH，RG=25Ω，ID=25A

5、The data is theoretically the same as I D and I DM , in real applications , should be limited by total power dissipation.

N-Typical Characteristics

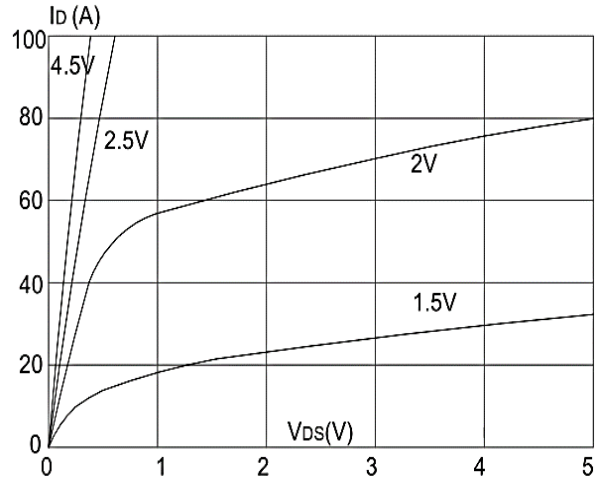


Figure1: Output Characteristics

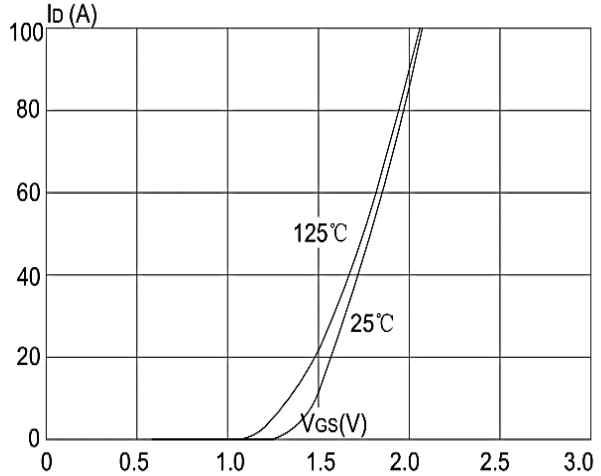


Figure 2: Typical Transfer Characteristics

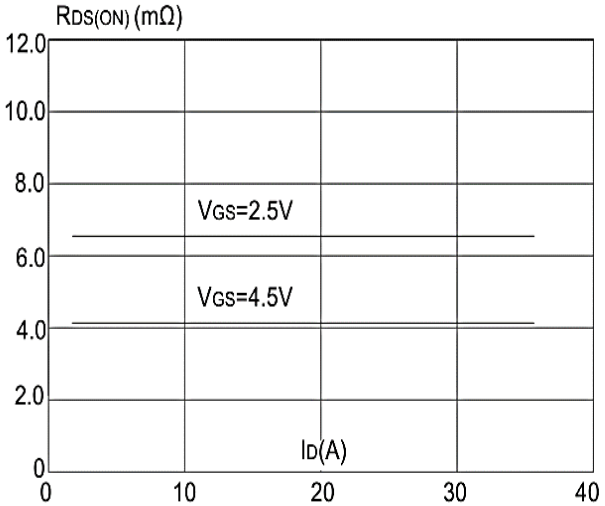


Figure 3:On-resistance vs. Drain Current

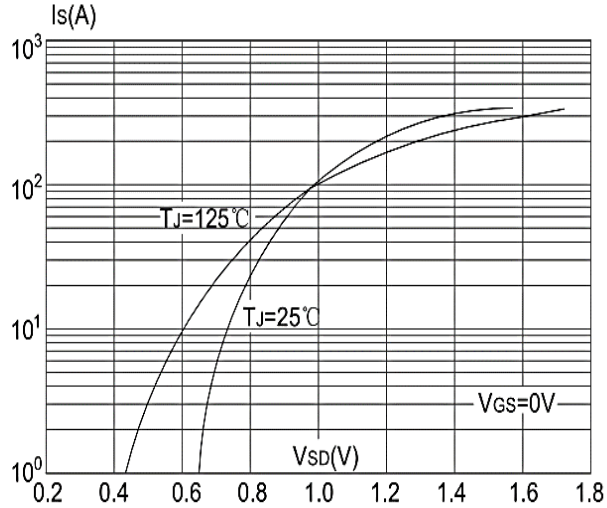


Figure 4: Body Diode Characteristics

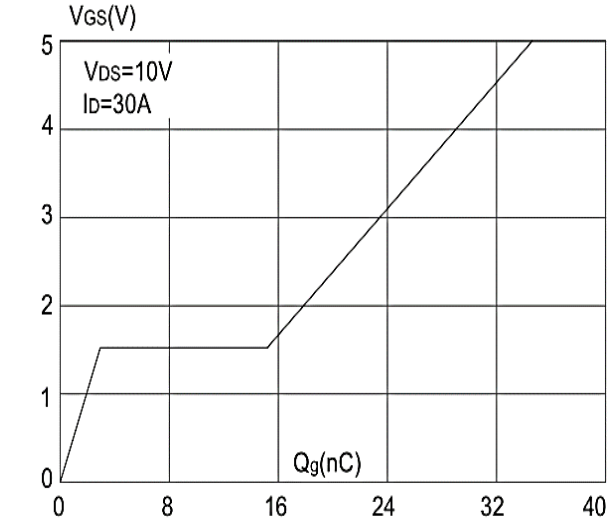


Figure 5: Gate Charge Characteristics

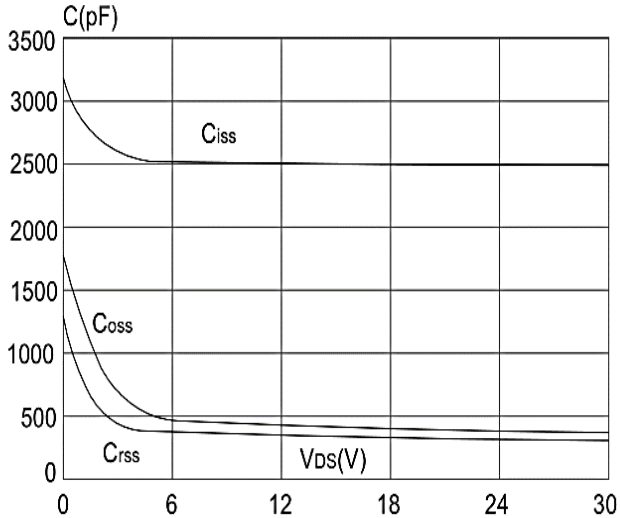


Figure 6: Capacitance Characteristics

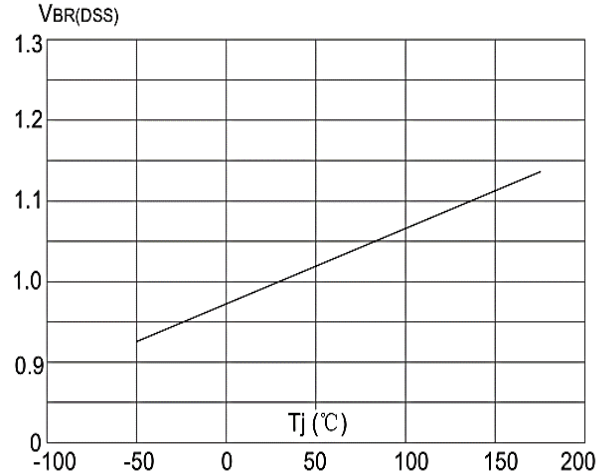


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

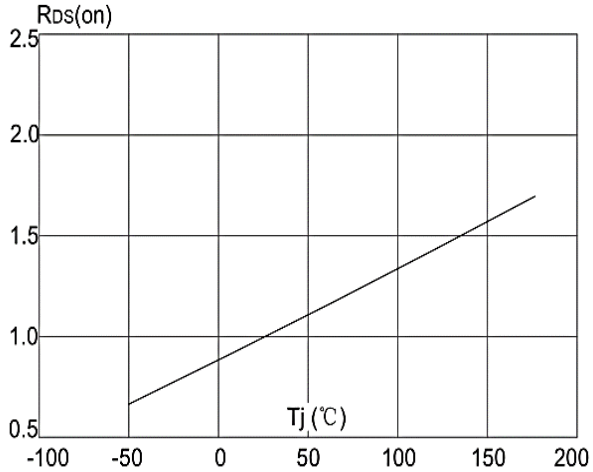


Figure 8: Normalized on Resistance vs Junction Temperature

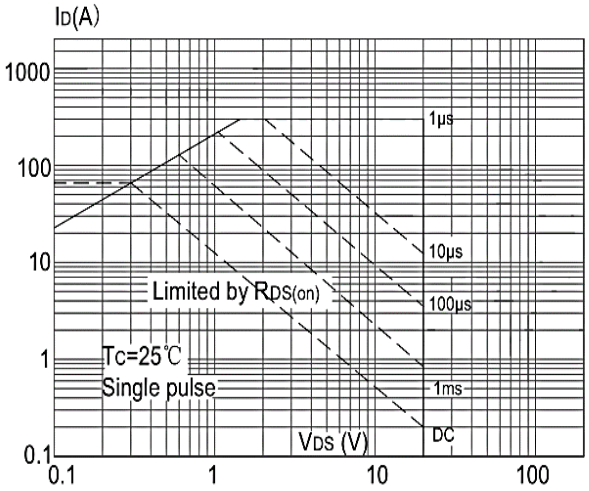


Figure 9: Maximum Safe Operating Area vs. Case Temperature

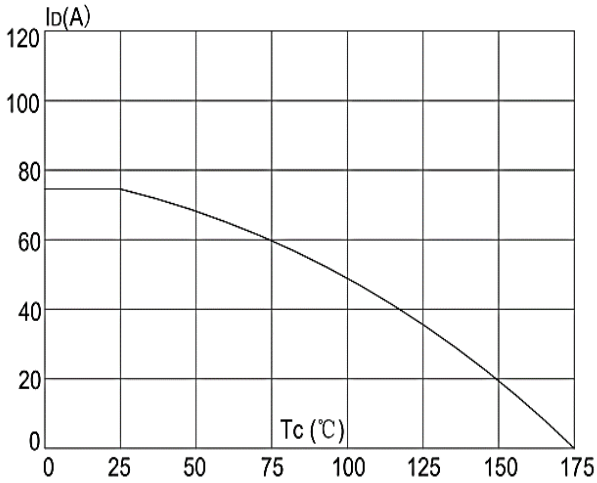


Figure 10: Maximum Continuous Drain Current

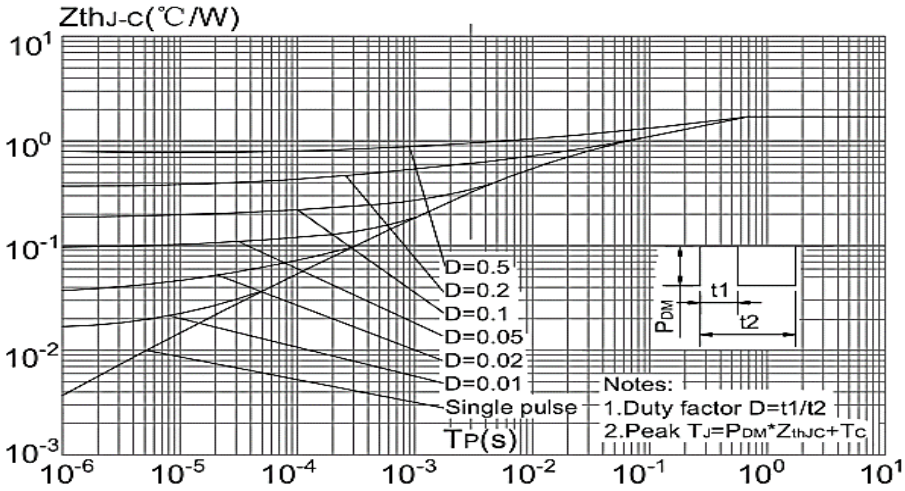


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

P-Typical Characteristics

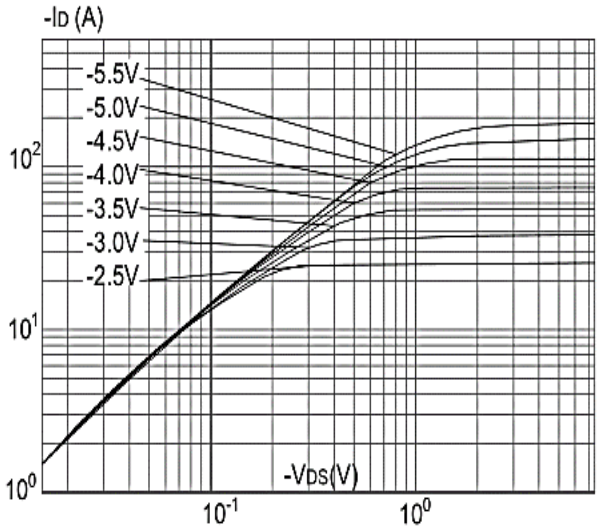


Figure1: Output Characteristics

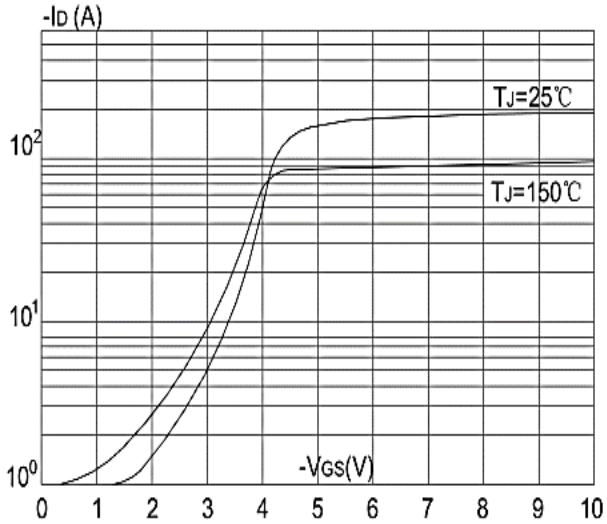


Figure 2: Typical Transfer Characteristics

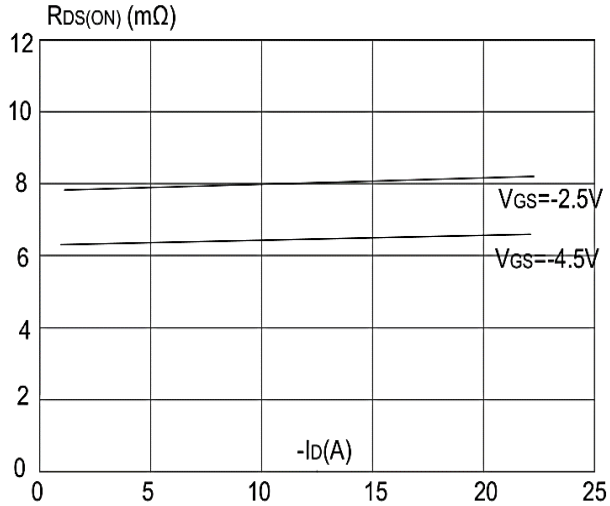


Figure 3:On-resistance vs. Drain Current

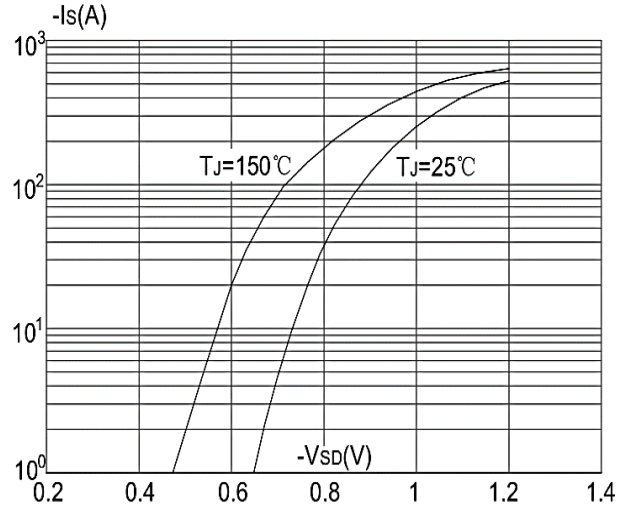


Figure 4: Body Diode Characteristics

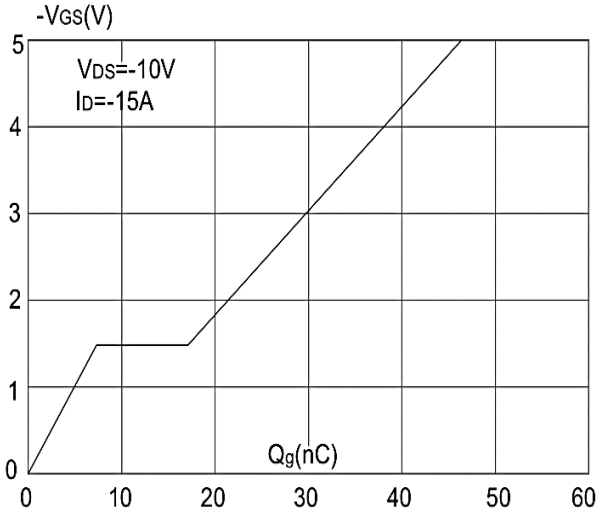


Figure 5: Gate Charge Characteristics

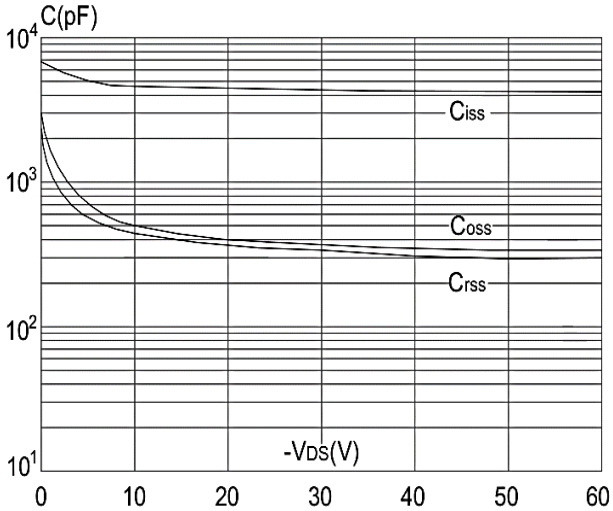


Figure 6: Capacitance Characteristics

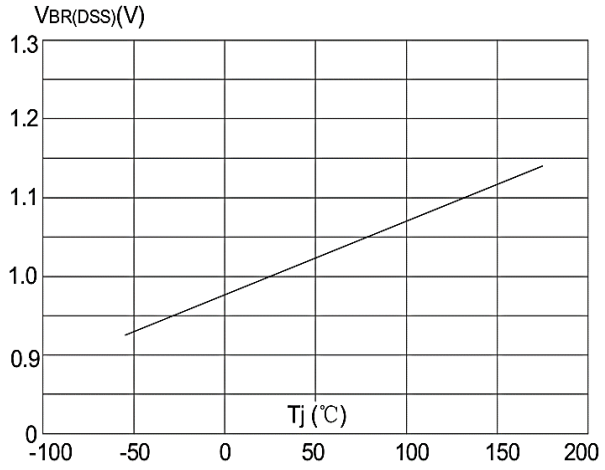


Figure 7: Normalized Breakdown Voltage vs Junction Temperature

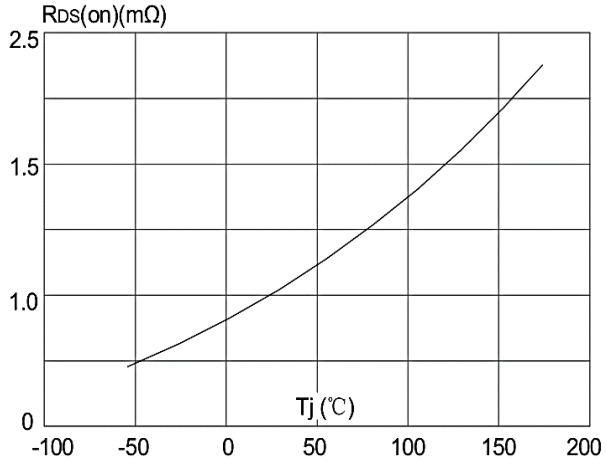


Figure 8: Normalized on Resistance vs. Junction Temperature

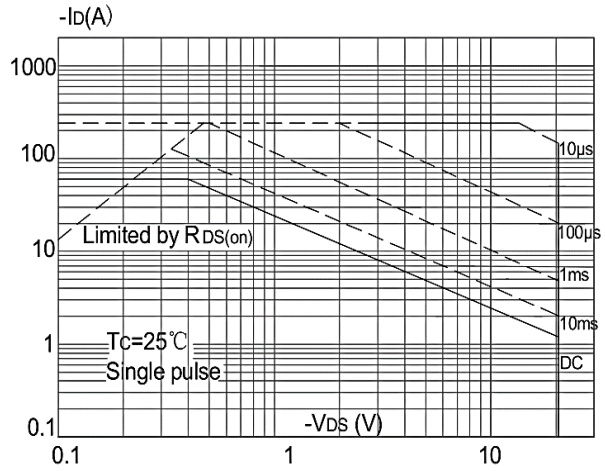


Figure 9: Maximum Safe Operating Area vs. Ambient Temperature

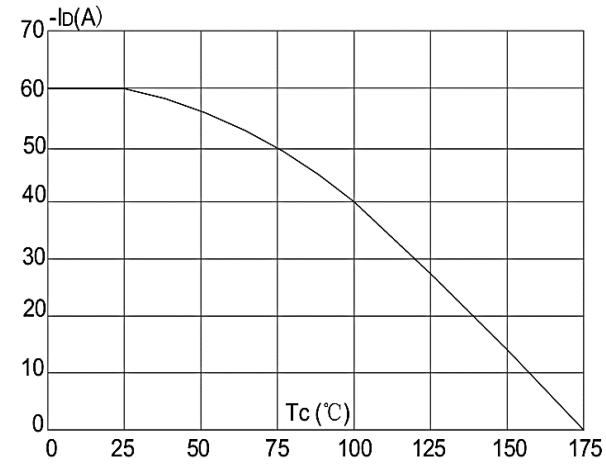


Figure 10: Maximum Continuous Drain Current

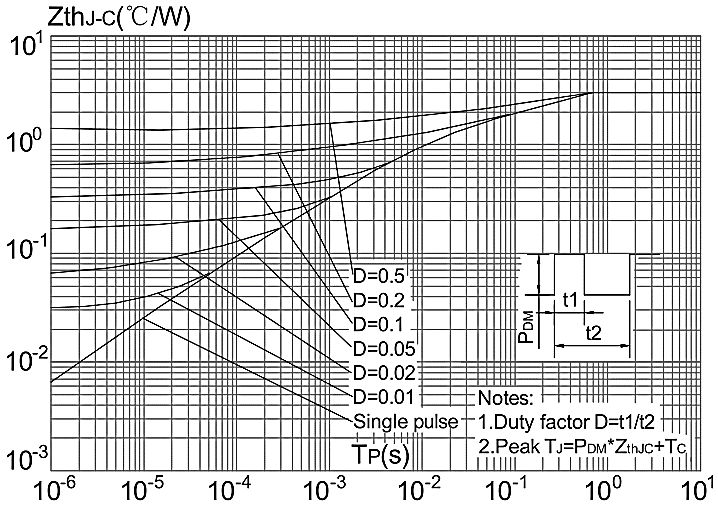
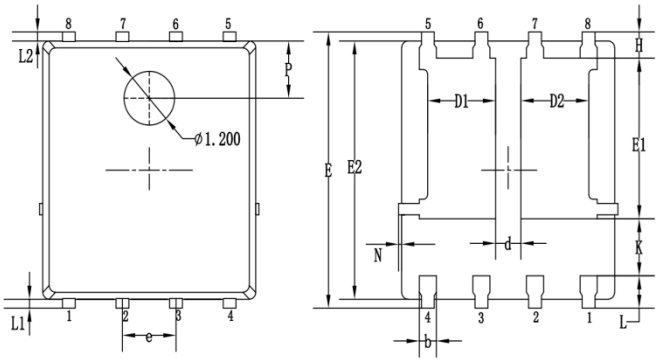
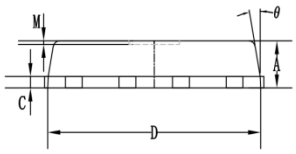


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambien

Package Mechanical Data-PDFN5*6-8L





Symbol	Dimensions In Millimeters		
	min.	typ.	max.
A	0.90	1.05	1.20
b	0.30	0.40	0.50
C	0.20	0.25	0.35
D	4.90	5.05	5.20
D1/D2	1.51	1.66	1.81
E	5.90	6.10	6.30
E1	3.30	3.50	3.70
E2	5.60	5.75	5.90
e	1.27BSC		
H	0.48	0.58	0.70
K	1.14	1.27	1.40
L	0.54	0.74	0.84
L1/L2	0.10	0.20	0.30
θ	8°	10°	12°
M	0.08REF		
N	0.00		0.15
P	1.28REF		
d	0.50	0.60	0.70

Attention

1,Any and all APM Microelectronics products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your APM Microelectronics representative nearest you before using any APM Microelectronics products described or contained herein in such applications.

2,APM Microelectronics assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all APM Microelectronics products described or contained herein.

3, Specifications of any and all APM Microelectronics products described or contained here instipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.

4, APM Microelectronics Semiconductor CO., LTD. strives to supply high quality high reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design,and structural design.

5,In the event that any or all APM Microelectronics products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.

6, No part of this publication may be reproduced or transmitted in any form or by any means,electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of APM Microelectronics Semiconductor CO., LTD.

7, Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production. APM Microelectronics believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.

8, Any and all information described or contained herein are subject to change without notice due to product/technology improvement,etc. When designing equipment, refer to the "Delivery Specification" for the APM Microelectronics product that you Intend to use.

Edition	Date	Change
REV1.0	2024/3/29	Initial release

Copyright Attribution "APM-Microelectronics"